**Deposition System Compatibility**

- Temperature 850°C Max, Vacuum Compatibility 10E-8 Torr to 1 Atm. Gases Ar, N2, He, H2, O2, CO2, C2H2, CH4, NH3, SiH4, and many Metal-Organic Precursors,
- Temperature Uniformity within 5-7%
- In-built K-type Thermocouple (TC)
- Sealed Heater Element and TC Against Gases and Plasma
- Stainless steel shield with tapped holes for sample Clamping and Heater Mounting

**Applications**

- Epitaxy of Oxides, Nitrides, Carbides, Metals
- Vacuum Annealing, Doping, Catalytic Reaction
- In-Situ Surface Science, R & D
- Graphene, CNTs, Diamond, and Thin Film
- Nanoelectronics, Optoelectronics, and Photonics
- Complex Multicomponent Multilayer Thin Films
- Gas Sensor and Device Temperature dependent Characterization

Std. 1.0”, 1.6”, 2.2”, 3.1”, 4.1”, and 6.1” OD diameter substrate heaters available for faster delivery!